



PATENT  
Customer No. 22,852  
Attorney Docket No. 04329.2306

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: )  
Yoshio OZAWA, et al. ) Group Art Unit: 2826  
Serial No.: 09/559,757 ) Examiner: Mondt, Johannes P.  
Filed: April 27, 2000 )  
For: SEMICONDUCTOR DEVICE AND )  
METHOD OF MANUFACTURE )  
THEREOF )

Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

AMENDMENT

Supplementary to the Request for Continued Examination (RCE) filed on May 29, 2002,  
please amend the application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

*Sub C1*

1. (Twice Amended) A semiconductor device comprising:  
a semiconductor substrate having a main plane in which a channel of a transistor is formed, the semiconductor substrate comprising a first region and a second region defined in a section taken along a direction of a channel length, the second region having a surface located lower than that of the first region, and the second region being connected to the first region;  
a gate insulating film formed on the first region and containing silicon, nitrogen and oxygen;

*H16/15  
JPD  
6/13/02*

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